Abstracts

COM2 enhanced graded base SiGe technology for high speed applications (2002 Vol. I [MWSYM])

T. Ivanov, M. Carroll, S. Moinian, M. Mastrapasqua, A. Frei, A. Chen, C. King, A. Hamad, E. Martin, S. Shive, T. Esry, C. Lee, R. Johnson, T. Sorsch, K. Banoo, P. Smith and W. Cochran.
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The COM2 enhanced graded base SiGe modular BiCMOS technology has been developed. It is based on the COM2 digital CMOS process. The technology achieves peak f/sub t/=100 GHz, peak f/sub max/=101 GHz, peak /spl beta/=186 and BV/sub cex/=2.05 V. An f/sub t/-BV/sub cex/ product of 205 and good across wafer uniformity are demonstrated.

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